POLITECNICO DI MILANO

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Advanced Course on

HIGH RESOLUTION ELECTRONIC MEASUREMENTS
IN NANO-BIO SCIENCE

Impedance Measurement Architectures and performance Marco Sampietro



Why measuring impedance values



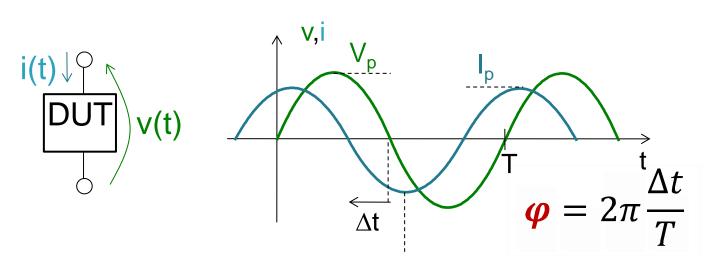
Mechanical **Electrical** DUT l(t) **Photonic** Magnetic **Biological**

Chemical

Extract R, L, C values in an electronic circuits ...

... access the conduction properties and the dissipative properties of a new device/material/molecule/etc.





Amplitude & Phase & Frequency

$$Z = \frac{V}{I}$$
 is a complex quantity

Impedance [Ohm]

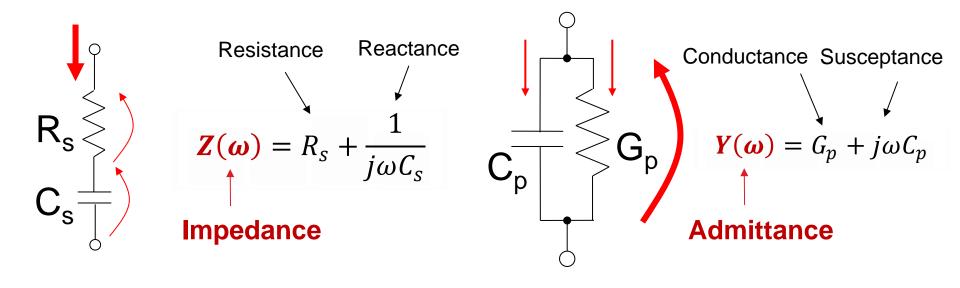


Admittance [Siemens]

$$V(t)$$
 $Y(\omega)$ $i(t)$



Impedance in terms of single R & C

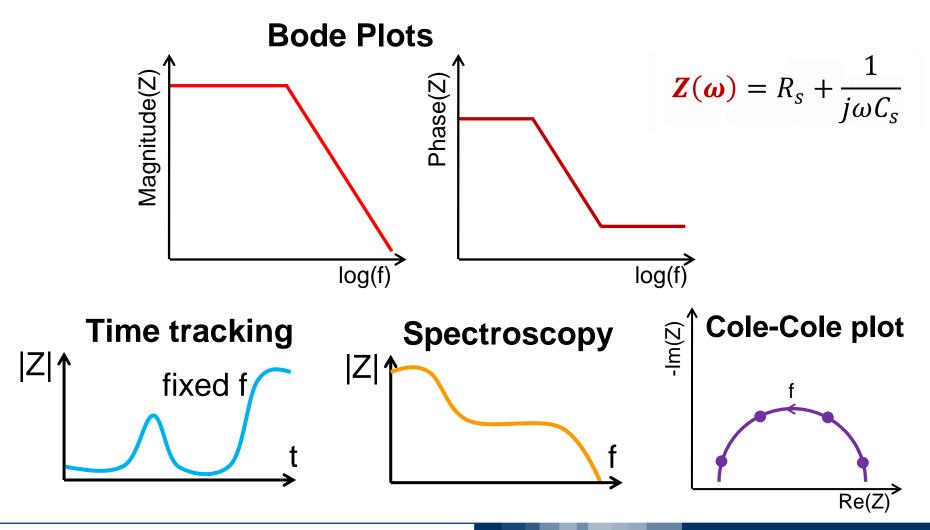


- Re{Z}, Re{Y} → energy dissipation (4kTRe{Z}, 4kTRe{Y})
- Im{Z}, Im{Y} → energy storage



Plotting the Impedance

Equivalent ways to plot impedance / admittance values





ChatGPT enquire

Myself: How can I measure the impedance of a device?

chatGPT: Using an Impedance Analyzer

Using an LCR Meter

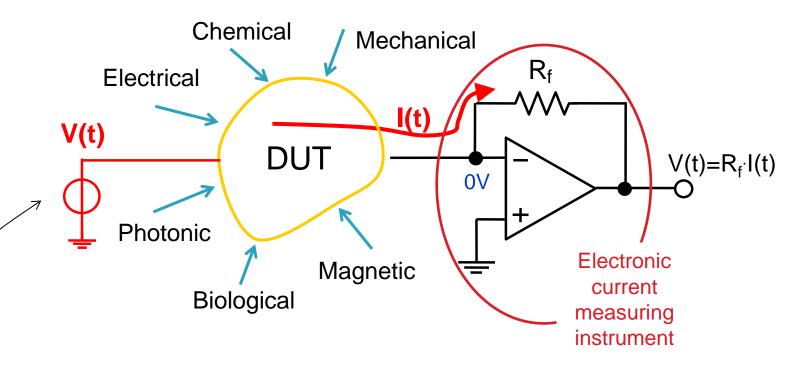
Lock-in architecture

Bridge Circuit

Oscilloscope and Function Generator using the voltagedivider principle



Lock-in configuration

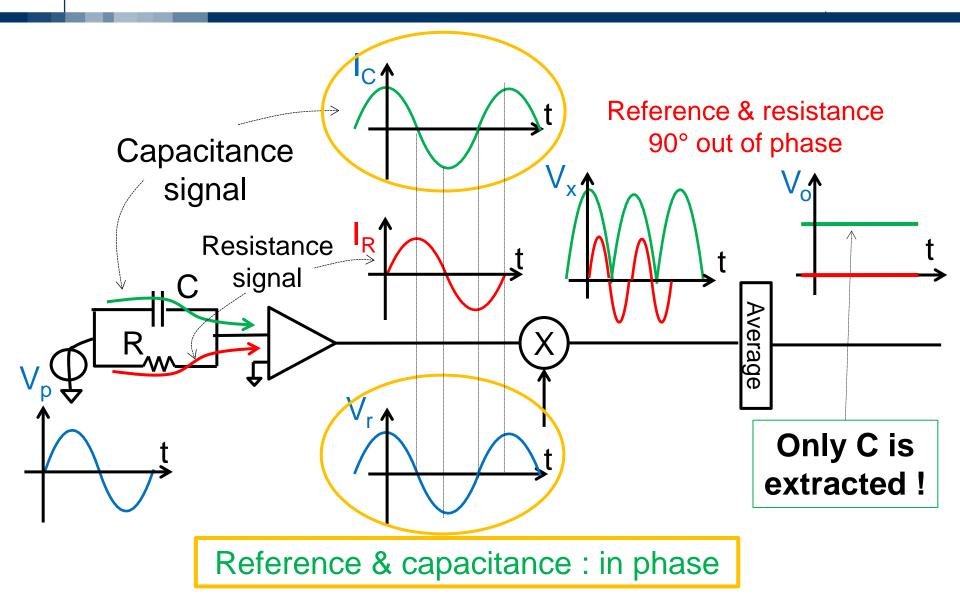


The Lock-in system is indeed ideal to perform IMPEDANCE measurements (and tracking it with time)

By sweeping the frequency, you can easily perform IMPEDANCE SPECTRUM

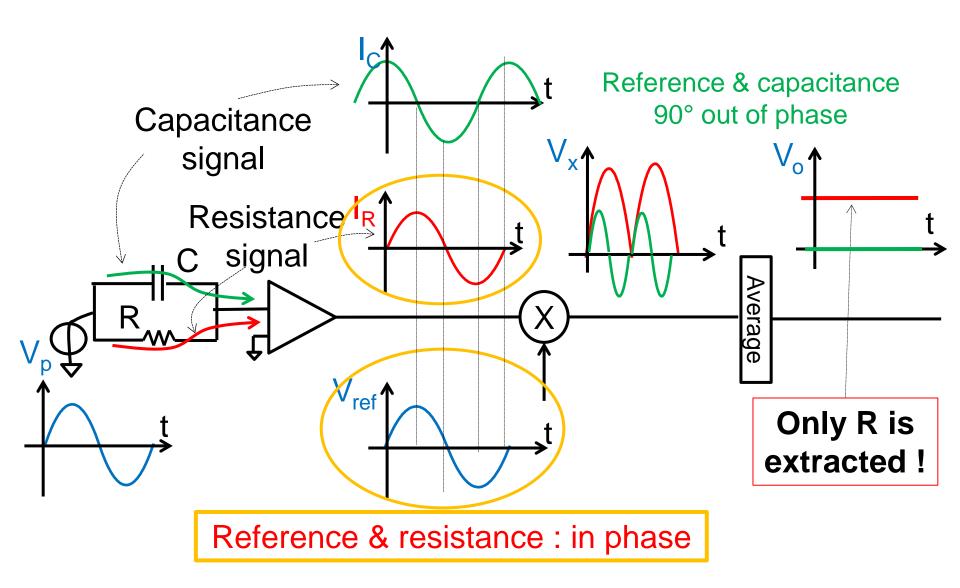


Mixture of R & C in real sensors





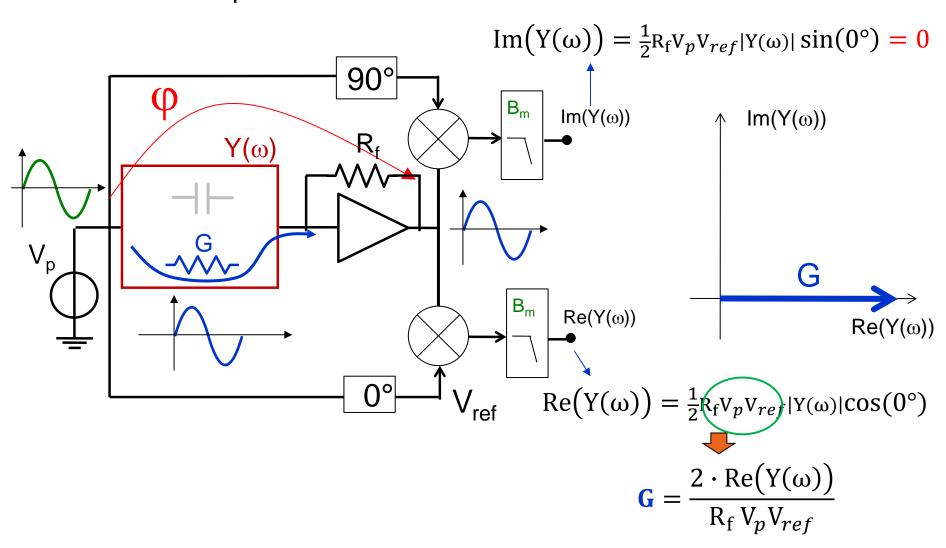
R & C selectivity of the LOCK-IN





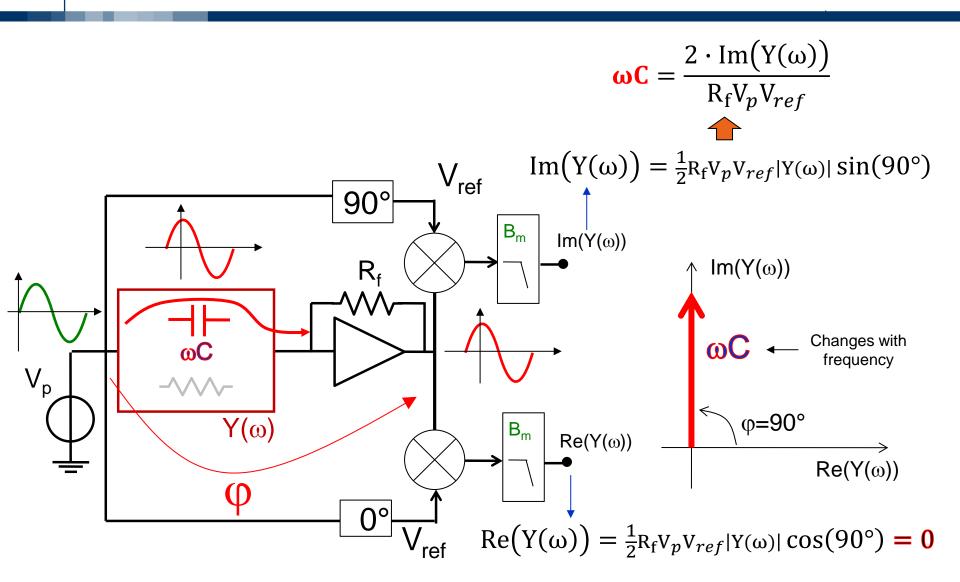
Double Lock-In: in-phase detection

Two multipliers are used to obtain both Re and Im of a DUT



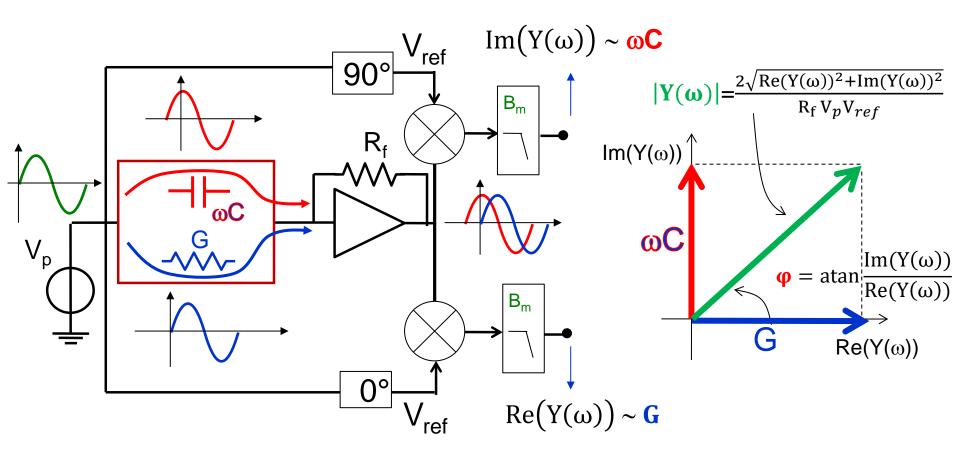


Double Lock-In: in-quadrature detect.



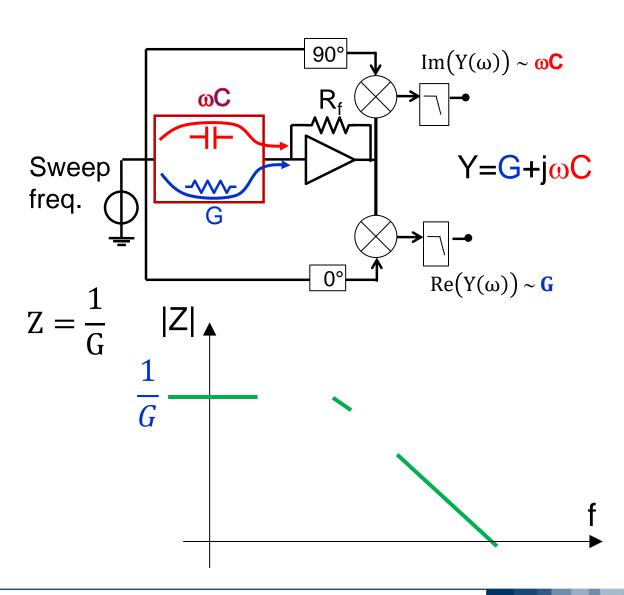


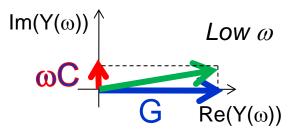
Lock-In: Impedance of R||C

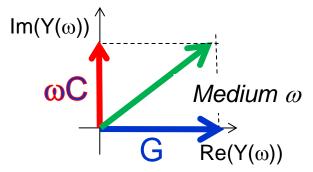


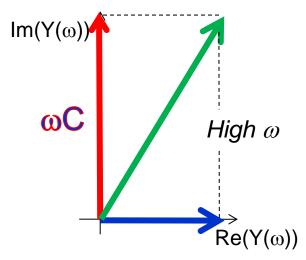


Sweeping the frequency: spectrum











Improving the resolution

You have a good set-up for the measurement of the capacitance of a DUT based on a lock-in platform. Using $V_p = V_{ref} = 0.1V$ and by averaging the measurement for $T_m = 30$ ms, you obtain a resolution of $\Delta C = 12$ aF in the sensor.

If a $\Delta C=1aF$ is required, what will you do?



$$\Delta C \propto \frac{1}{\sqrt{T_m}}$$

$$T_m=30ms$$
 $T_m=4.3s$

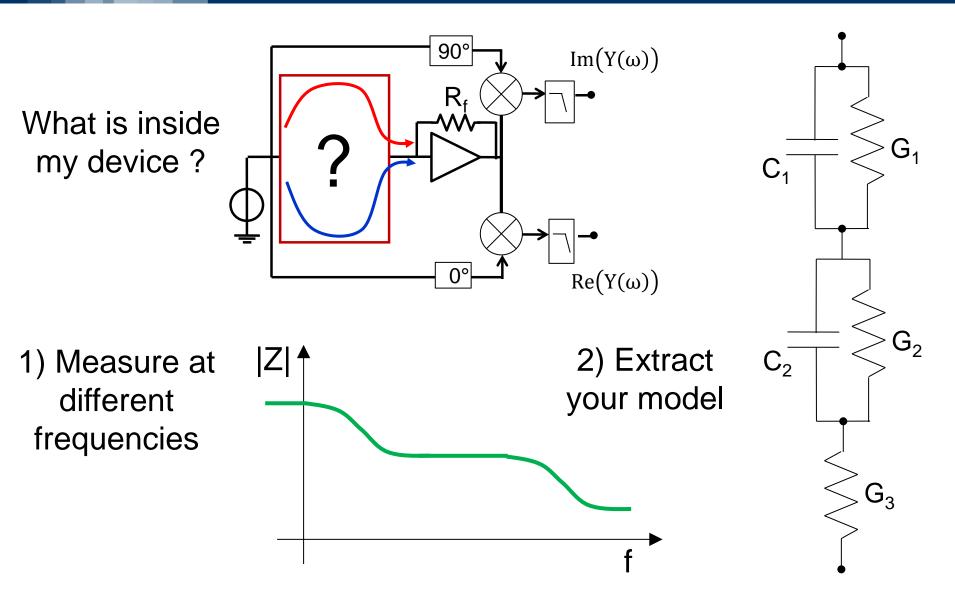
Increase the amplitude of V_p or V_{ref} or both

$$\Delta \omega \mathbf{C} \propto \frac{1}{\mathrm{R_f V}_p \mathrm{V}_{ref}}$$

$$V_{ref}=0.1V \longrightarrow V_{ref}=1.2V$$



Extracting elements from a spectrum



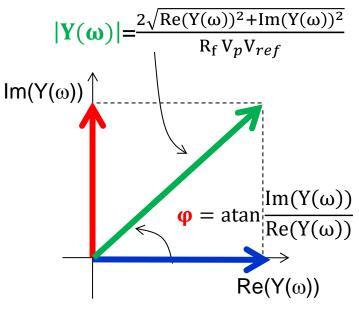


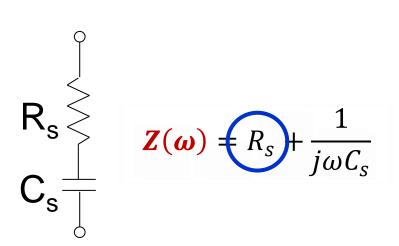
Pre-defined models in LCR meters

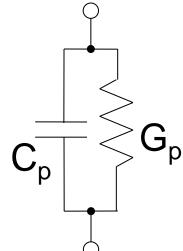


You select the model.

The instrument gives you the R & C values





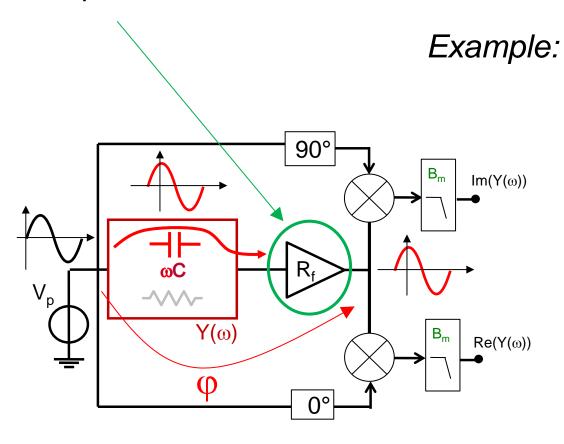


$$Y(\omega) \neq G_p + j\omega C_p$$



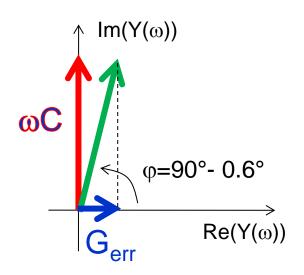
Calibration

Amplifiers and connections introduce errors in amplitude and phase



<u>Ideal calibration</u>: with a known sample (amplitude and phase)

C=1pF at 1MHz
Phase error 0.6°
(a pole distant two decades)

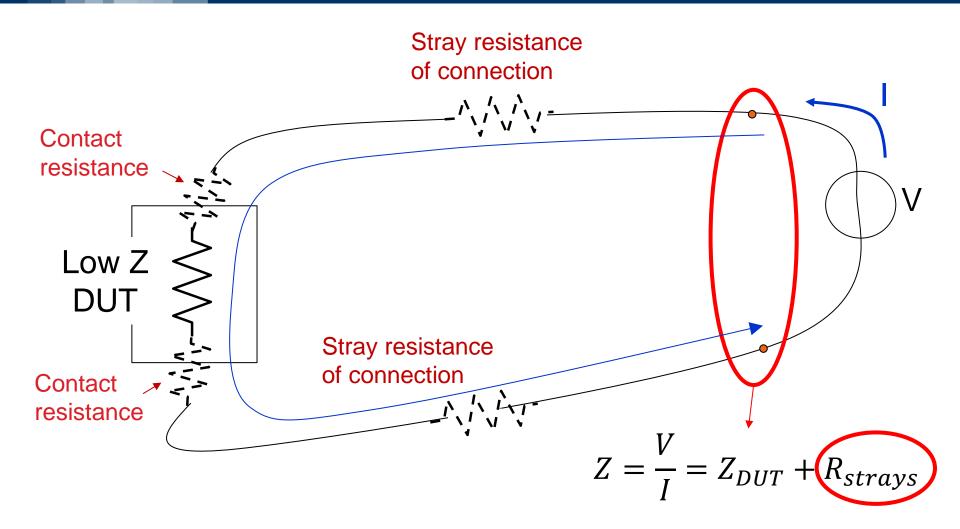


 $G_{err} = \omega C_x \sin(0.6^\circ) = 6.10^{-8} \text{ S}$ (16M Ω , to be compared with ∞)

If $\phi_{err}=10^{\circ}$ than $1/G_{err}=1M\Omega$!

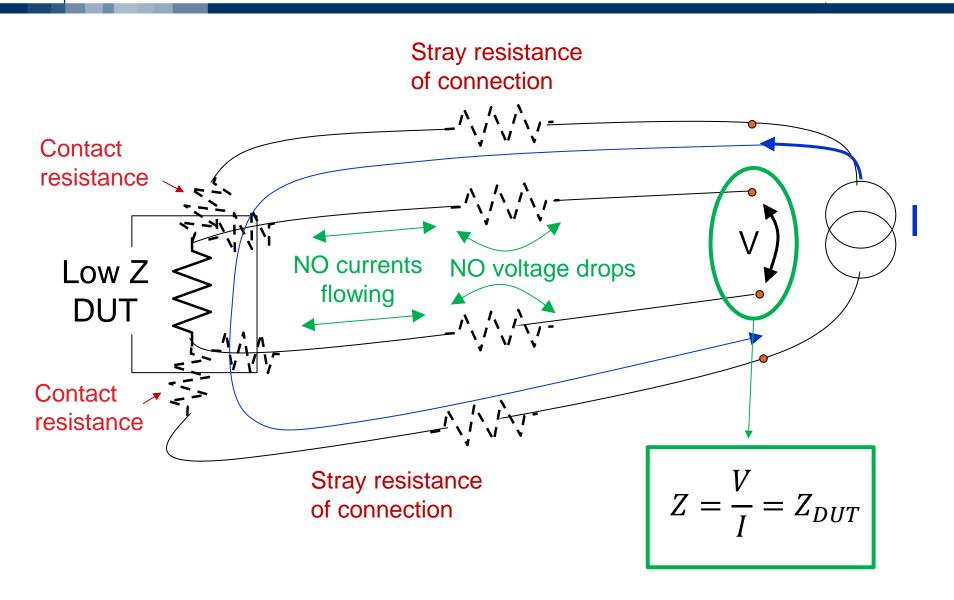


Contribution of strays (resistances)



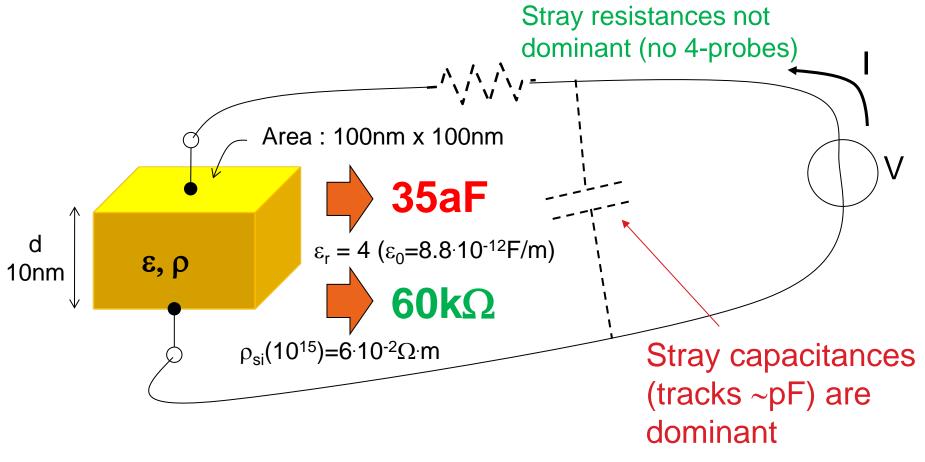


4 probes Impedance measurement





Impedance at the Nanoscale

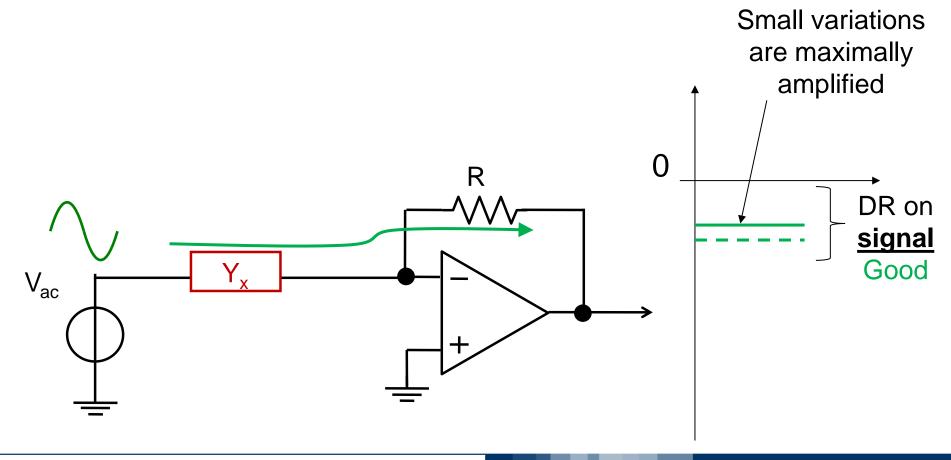


$$\tau = RC = \rho \frac{d}{Area} \cdot \varepsilon \frac{Area}{d}$$

 $\tau = \rho \cdot \varepsilon = 2ps$ *independent* of size



Problems given by strays (capacitance)





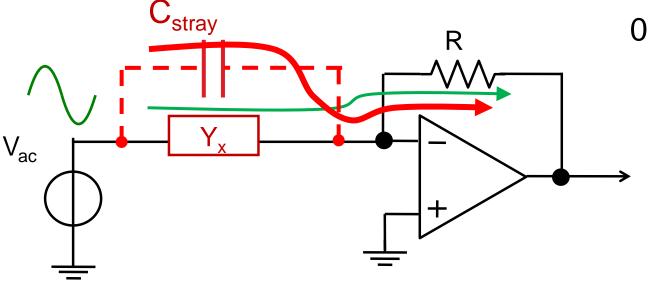
Reduction of sensitivity

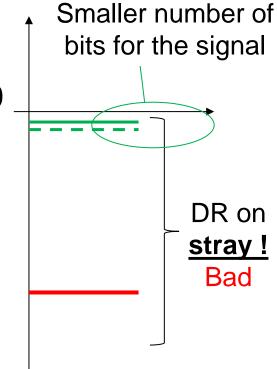
A stray parallel capacitance C_{stray} may:

saturate the front-end or gain stages

Reduce gain \Rightarrow reduce resolution

require ADC with large bit number

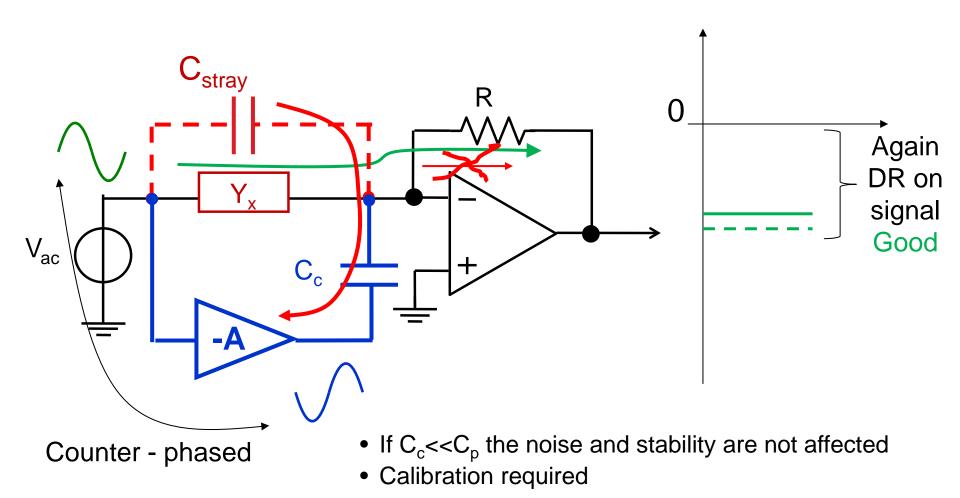






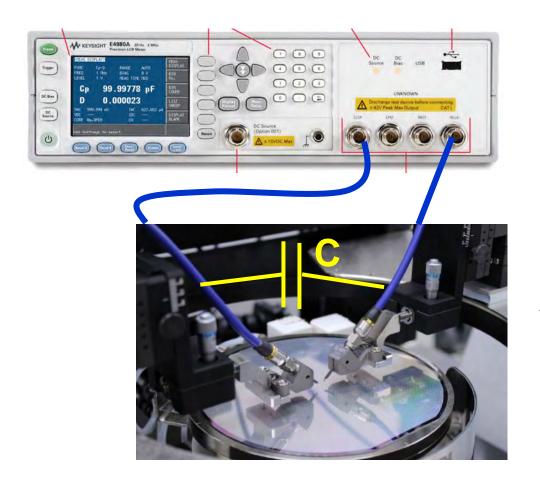
Compensation in current sensing

An active capacitance compensation can be useful:





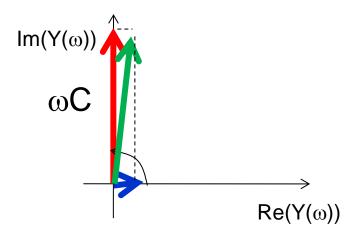
Strays compensation in LCR meter (1



OPEN
You Lift the probes (a little)

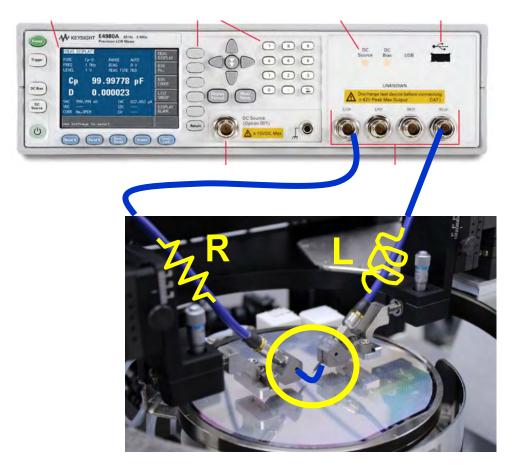
The instrument:

- Measures (the strays, mainly capacitance)
- Memorizes the values *Re* and *Im* at different f
- Correct the following meas. with these values





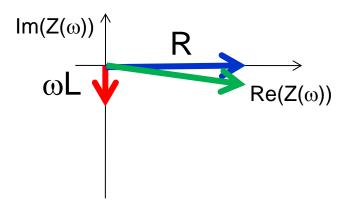
Strays compensation in LCR meter (2



SHORT You Put probes in contacts

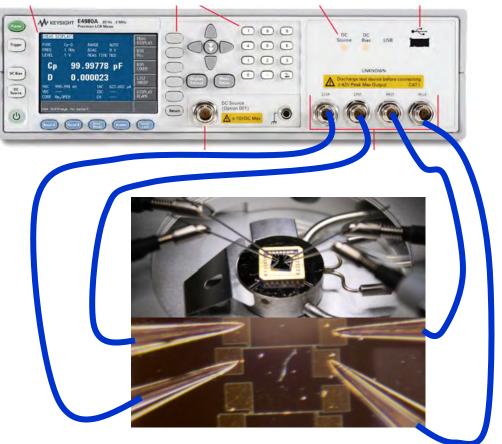
The instrument

- Measures (the strays, mainly resistance-inductance)
- Memorizes the values *Re* and *Im* at different f
- Correct the following meas. with these values





Strays compensation in LCR meter (3



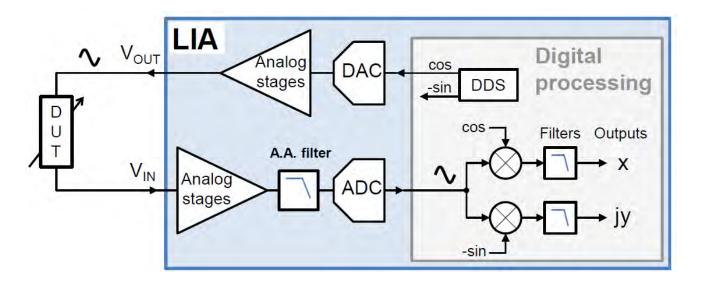
In addition USE 4 PROBES



Digital LOCK-IN amplifiers

Impedance spectroscopy with lock-in requires a separate measurement for each frequency → long time

Alternatives: Apply many-frequencies as stimulus and process in parallel;
Apply white noise at input and calculate the DFT of signals.



Next lesson by Giorgio Ferrari



Myself: How can I measure the impedance of a device?

chatGPT: Using an Impedance AnalyzerUsing an LCR Meter

Lock-in architecture

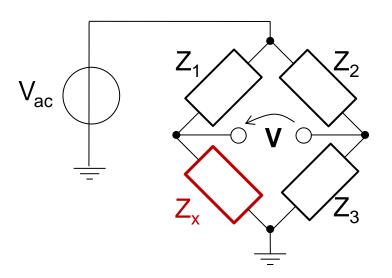
Bridge Circuit

Oscilloscope and Function Generator using the voltagedivider principle

Material follows for your convenience



Balancing Bridge: Working Principle



- Z₁, Z₂, Z₃ known and variable (switches)
- V_{ac} sinusoidal

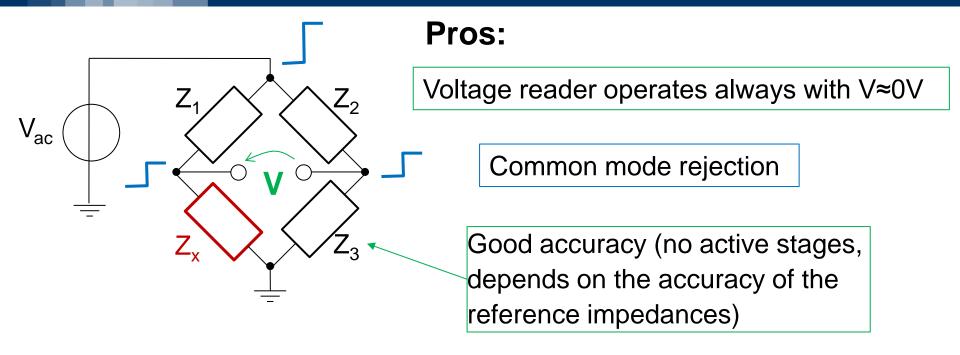
$$V = V_{ac} \left(\frac{Z_x}{Z_1 + Z_x} - \frac{Z_3}{Z_2 + Z_3} \right)$$



Balanced for
$$\mathbf{V} = \mathbf{0}$$
 $\mathbf{Z}_{x} = Z_{3} \frac{Z_{1}}{Z_{2}}$



Bridge Pros and Cons



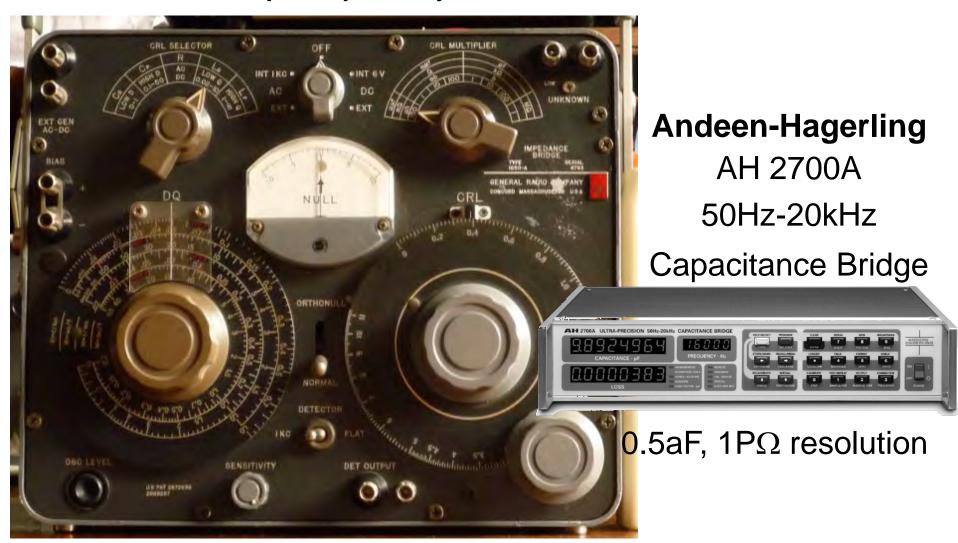
Cons:

- Requires several switches
- Slow balancing routine
- Not very convenient for spectroscopy



Examples of Commercial Instruments

GR 1650-A (1957) ...fully manual

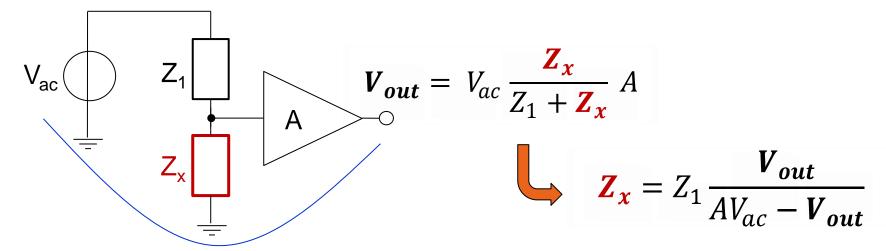




Ratiometric: Half Bridge

Ratiometric i.e. V_{out} depends on the impedance ratio

Independent of the absolute value



A phase sensitive detector is needed

Z₁ has to be accurate (wide dynamic) :

•
$$Z_x >> Z_1$$
: $V_{out} \approx AV_{ac}$
• $Z_x << Z_1$: $V_{out} \approx 0$ $Z_1 \sim Z_x$

•
$$Z_x << Z_1$$
: $V_{out} \approx 0$

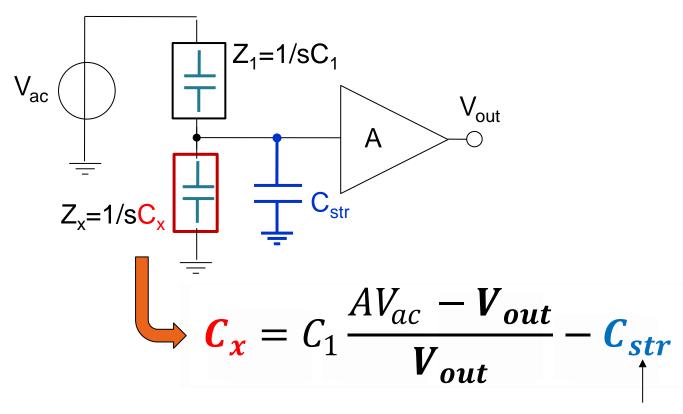


$$Z_1 \sim Z_x$$

Difficult at the nanoscale



Capacitance detection: Effect of Cstray

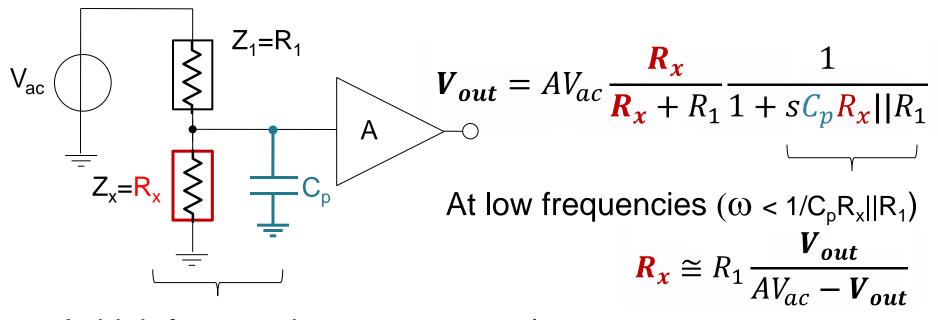


Reduces the accuracy!

DC bias of Z_x not defined



Resistance detection: Effect of Cstray



At high frequencies ($\omega > 1/C_pR_x||R_1$)

 \rightarrow R_x shunted by C_p!

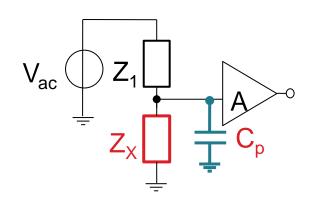
Example: a cube of intrinsic Si (\sim 1k Ω cm), side = 50nm \rightarrow R_x = 200M Ω , cut-off frequency = 160Hz (C_p = 5pF)



Comparison

Ratiometric:

- C_p limits bandwidth and accuracy
- No control of the voltage applied to Z_x
- Z₁ must match Z_x



Current sensing:

- Independent of C_p (wide-band opamp)
- Precise control of the voltage applied
- Need to access both terminals of Z_x
- Loop stability depends on Z_x (but at the nanoscale dominated by stray capacitance ≈ known)

In terms of resolution they are equivalent

